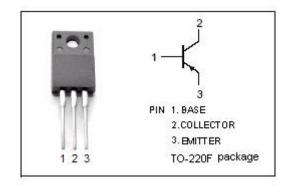


# **isc Silicon PNP Power Transistor**

2SA1931

### **DESCRIPTION**

- Low Collector Saturation Voltage-
  - : V<sub>CE(sat)</sub>= -0.4V(Max.)@I<sub>C</sub>= -3A
- High Switching Speed
- Complement to Type 2SC3299
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



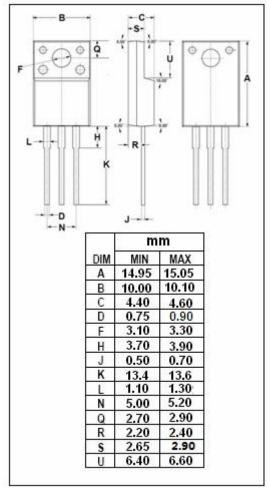


### **APPLICATIONS**

Designed for high current switching applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	-60	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-60	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
lc	Collector Current-Continuous	-5	Α
I <sub>B</sub>	Base Current-Continuous -1		Α
P <sub>C</sub>	Collector Power Dissipation @T <sub>a</sub> =25℃	2	W
	Collector Power Dissipation @T <sub>C</sub> =25℃	25	VV
TJ	Junction Temperature	150	$^{\circ}$ C
T <sub>stg</sub>	Storage Temperature	-55~150	$^{\circ}$ C





## **isc Silicon PNP Power Transistor**

2SA1931

#### **ELECTRICAL CHARACTERISTICS**

Tj=25℃ unless otherwise specified

	nooo otnorwoo opoomoa					
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -10mA; I <sub>B</sub> = 0	-60			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -3A; I <sub>B</sub> = -0.15A			-0.4	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = -3A; I <sub>B</sub> = -0.15A			-1.2	V
Ісво	Collector Cutoff Current	V <sub>CB</sub> = -50V; I <sub>E</sub> = 0			-1.0	μ <b>А</b>
I <sub>ЕВО</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0			-1.0	μ <b>А</b>
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -1A; V <sub>CE</sub> = -1V	70		240	
h <sub>FE-2</sub>	DC Current Gain	Ic= -3A; Vc== -1V	30			
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = -1A; V <sub>CE</sub> = -4V		60		MHz
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = -10V; f= 1MHz		230		pF
Switching Times						
ton	Turn-On Time			0.1		μ <b>S</b>
t <sub>stg</sub>	Storage Time	I <sub>B1</sub> = -I <sub>B2</sub> = -0.15A; V <sub>CC</sub> = -30V;   R <sub>L</sub> = 10 Ω; Duty Cycle≤1%		1.0		μ <b>S</b>
tf	Fall Time	, , , , , , , , , , , , , , , , , , , ,		0.1		μs

## ♦ h<sub>FE-1</sub> Classifications

0	Y
70-140	120-240

#### Notice:

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